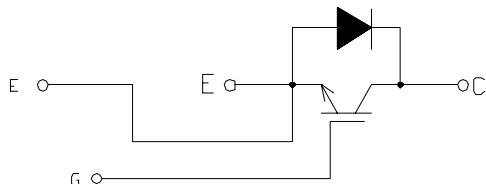


TENTATIVE

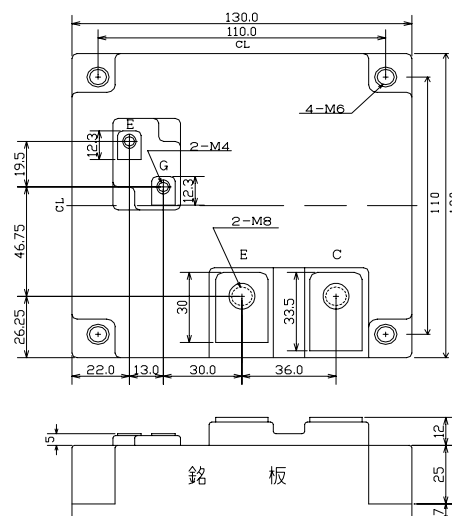
# IGBT MODULE Single 1200A 1200V

# PHMB1200B12

## CIRCUIT



## OUTLINE DRAWING



4 - fasten- tab No 110

Dimension(mm)

Approximate Weight : 1,200g

MAXMUM RATINGS (T<sub>c</sub>=25°C)

Item		Symbol	PHMB1200B12		Unit
Collector-Emitter Voltage		V <sub>CEs</sub>	1200		V
Gate - Emitter Voltage		V <sub>GES</sub>	+/- 20		V
Collector Current	DC	I <sub>C</sub>	1200		A
	1 ms	I <sub>CP</sub>	2400		
Collector Power Dissipation		P <sub>C</sub>	5600		W
Junction Temperature Range		T <sub>j</sub>	-40 to +150		°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +125		°C
Isolation Voltage Terminal to Base AC, 1 min.)		V <sub>ISO</sub>	2500		V
Mounting Torque	Module Base to Heat sink	F <sub>TOR</sub>	3		N•m
	Bus Bar to Main Terminals		M4	1.4	
			M8	10.5	

ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Emitter Cut-Off Current		I <sub>CEs</sub>	V <sub>CE</sub> =1200V, V <sub>GE</sub> =0V	-	-	24	mA
Gate-Emitter Leakage Current		I <sub>GES</sub>	V <sub>GE</sub> =+/- 20V, V <sub>CE</sub> =0V	-	-	1.0	μA
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>	I <sub>C</sub> =1200A, V <sub>GE</sub> =15V	-	1.9	2.4	V
Gate-Emitter Threshold Voltage		V <sub>GE(th)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =400mA	4.0	-	8.0	V
Input Capacitance		C <sub>ies</sub>	V <sub>CE</sub> =10V, V <sub>GE</sub> =0V, f=1MHz	-	100000	-	pF
Switching Time	Rise Time	t <sub>r</sub>	V <sub>CC</sub> = 600V R <sub>L</sub> = 0.5 ohm R <sub>C</sub> = 0.33 ohm V <sub>GE</sub> = +/- 15V	-	0.25	0.45	μs
	Turn-on Time	t <sub>on</sub>		-	0.40	0.70	
	Fall Time	t <sub>f</sub>		-	0.25	0.35	
	Turn-off Time	t <sub>off</sub>		-	1.00	1.50	

FREE WHEELING DIODES RATINGS & CHARACTERISTICS (T<sub>c</sub>=25°C)

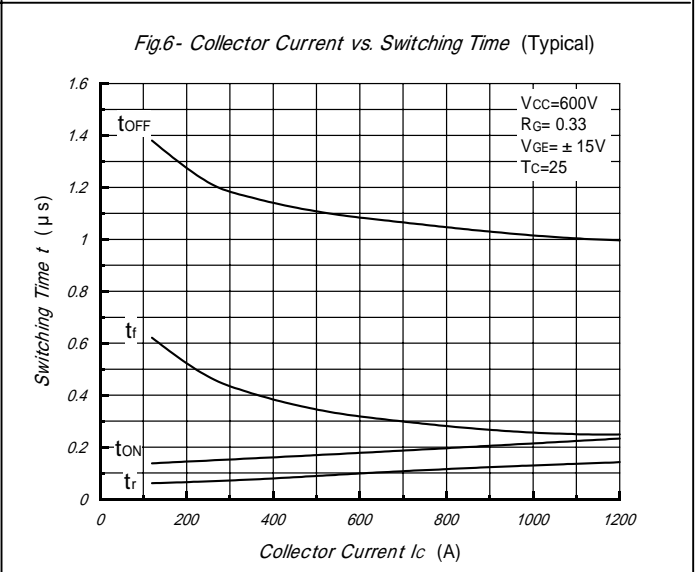
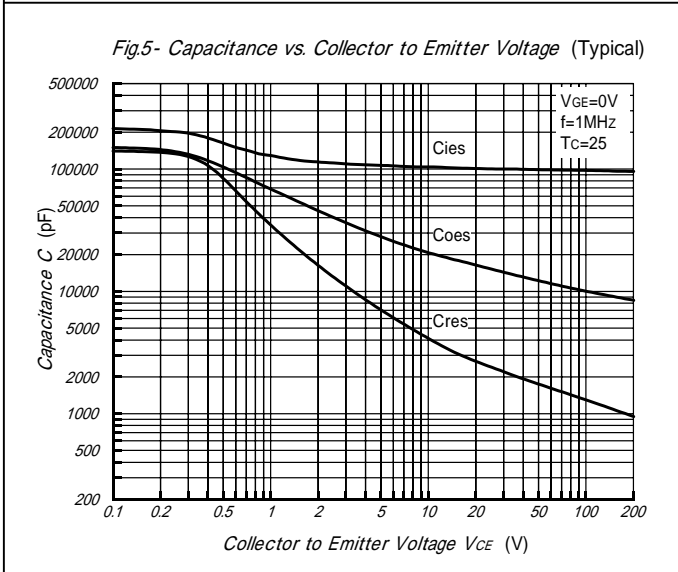
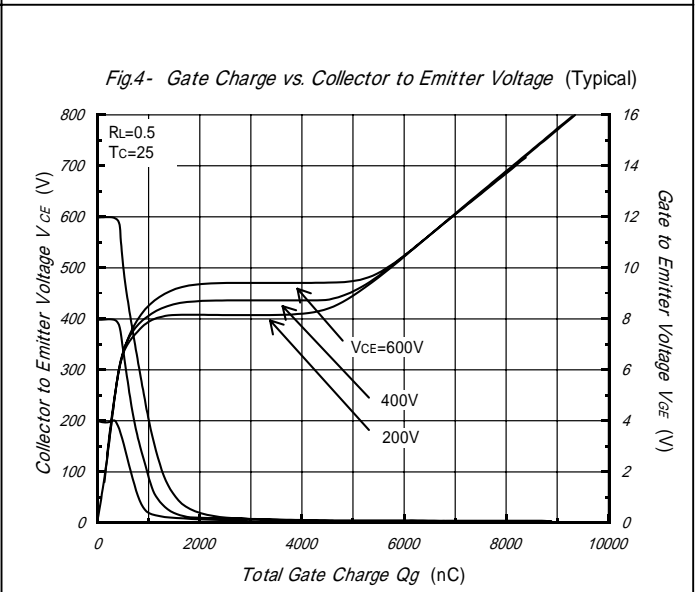
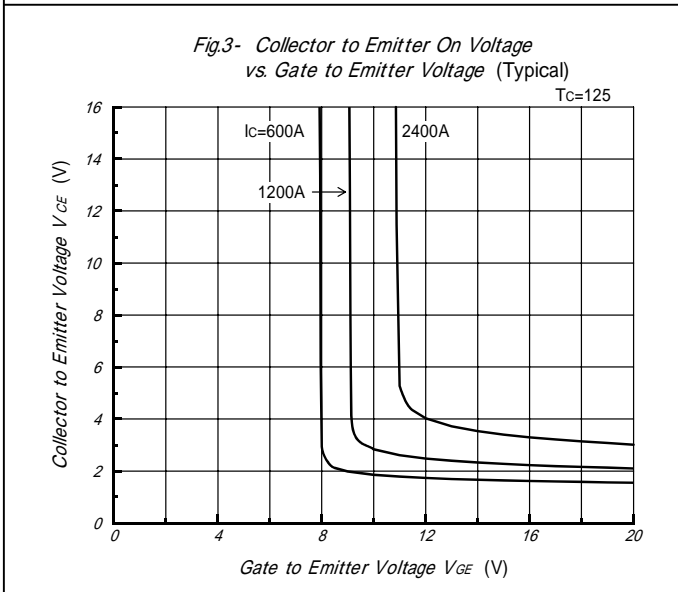
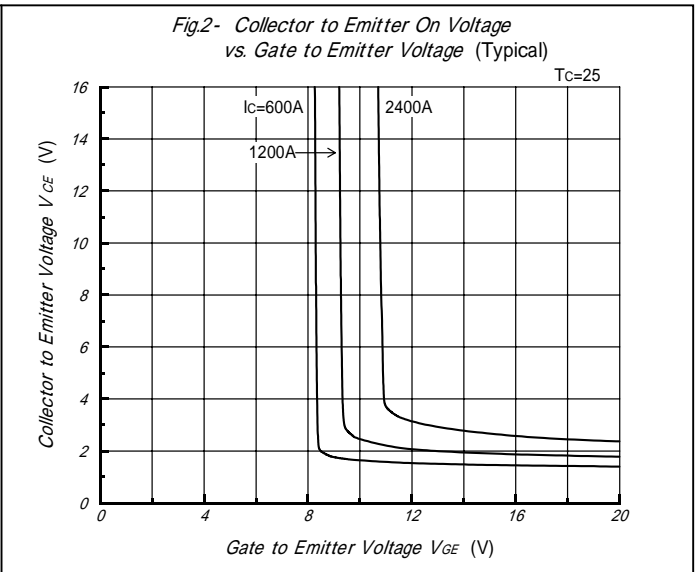
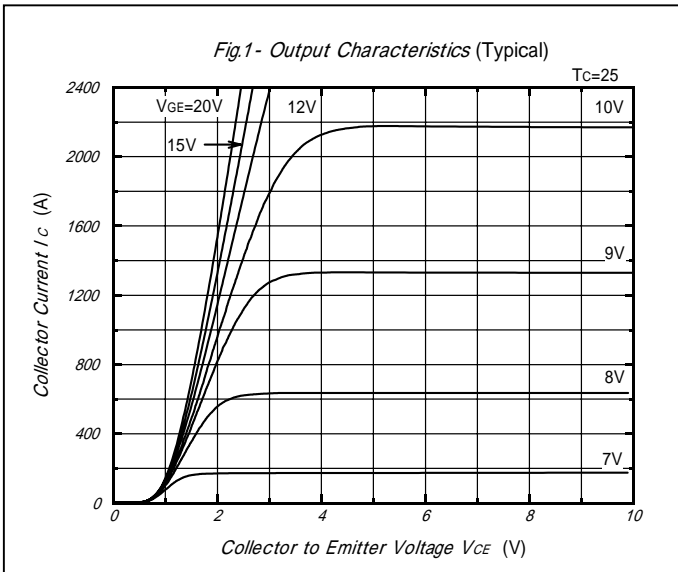
Item		Symbol	Rated Value		Unit
Forward Current	DC	I <sub>F</sub>	1200		A
	1 ms	I <sub>FM</sub>	2400		

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Peak Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =1200A, V <sub>GE</sub> =0V	-	1.9	2.4	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =1200A, V <sub>GE</sub> =-10V, di/dt=2400A/μs	-	0.4	0.5	μs

## THERMAL CHARACTERISTICS

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Thermal Impedance	IGBT	R <sub>th(j-c)</sub>	Junction to Case	-	-	0.022	°C/W
	DIODE			-	-	0.043	

PHMB1200B12



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Fig.7- Series Gate Impedance vs. Switching Time (Typical)

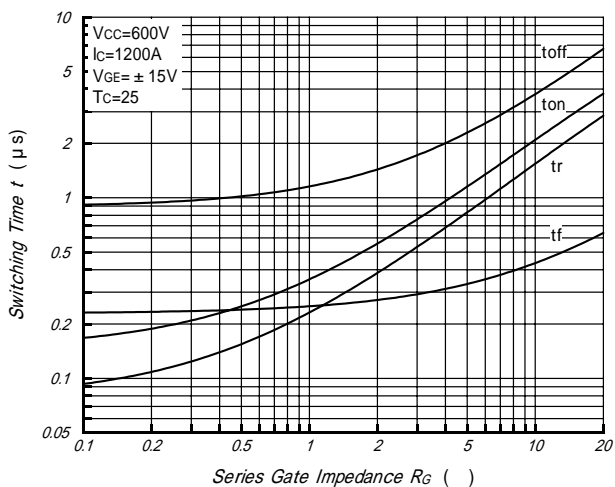


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

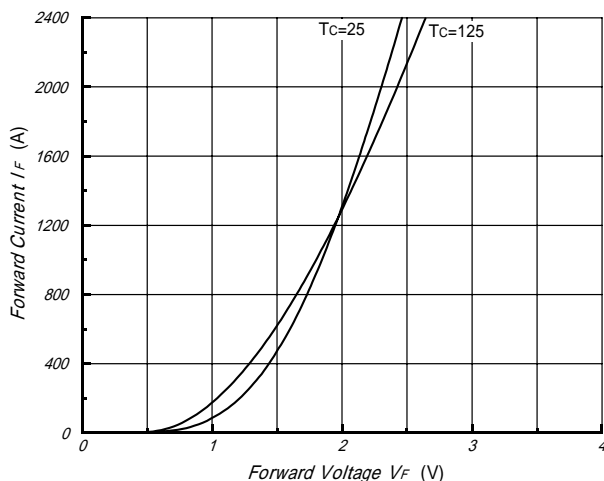


Fig.9- Reverse Recovery Characteristics (Typical)

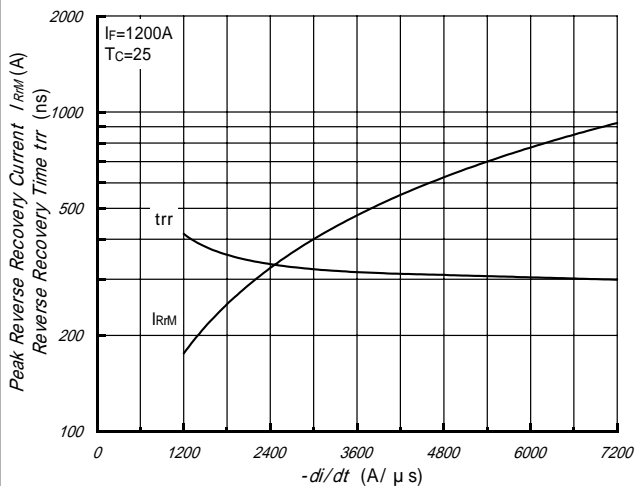


Fig.10- Reverse Bias Safe Operating Area (Typical)

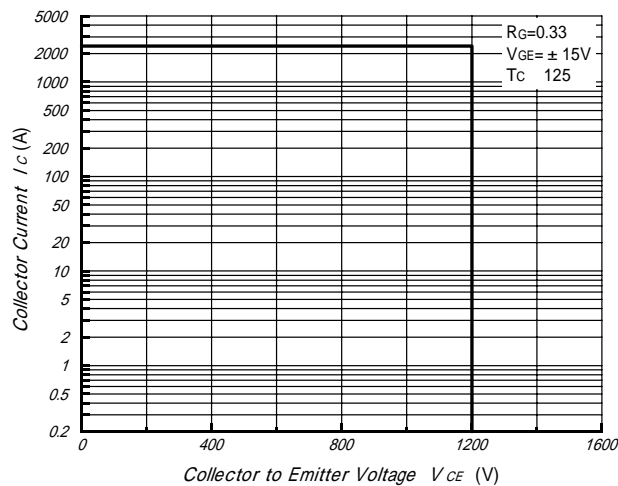


Fig.11- Transient Thermal Impedance

